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(54) Title: ETCH FEEDBACK FOR CONTROL OF UPSTREAM PROCESS

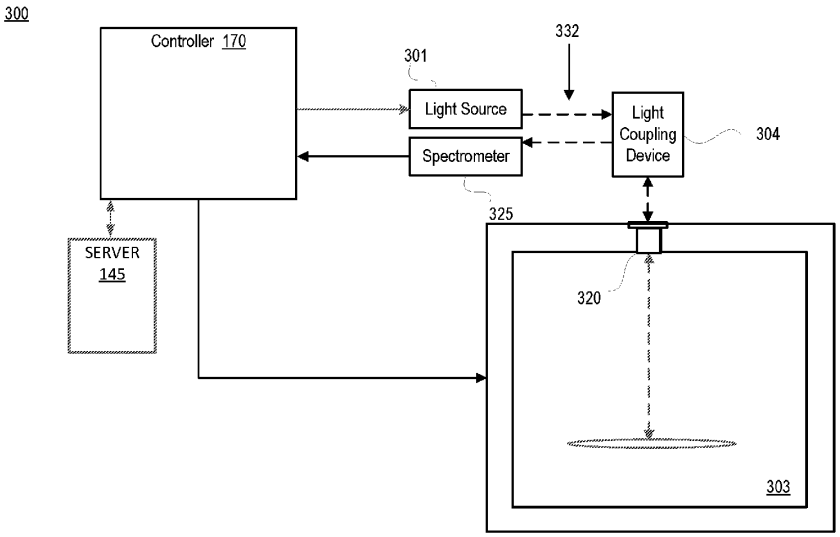


FIG. 3

(57) Abstract: A substrate processing system comprises an etch chamber configured to perform an etch process on a substrate, the etch chamber comprising an optical sensor to generate one or more optical measurements of a film on the substrate during and/or after the etch process. The system further comprises a computing device operatively connected to the etch chamber, wherein the computing device is to: receive the one or more optical measurements of the film; determine, for each optical measurement of the one or more optical measurements, a film thickness of the film; determine an etch rate of the film based on the one or more optical measurements using the determined film thickness of each optical measurement of the one or more optical measurements; and determine a process parameter value of at least one process parameter for a previously performed process that was performed on the substrate based on the etch rate.

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— *as to the applicant's entitlement to claim the priority of the earlier application (Rule 4.17(iii))*

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